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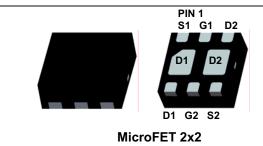


# FDMA1028NZ

## Dual N-Channel PowerTrench<sup>®</sup> MOSFET

### **General Description**

This device is designed specifically as a single package solution for dual switching requirements in cellular handset and other ultra-portable applications. It features two independent N-Channel MOSFETs with low on-state resistance for minimum conduction losses. The MicroFET 2x2 package offers exceptional thermal performance for its physical size and is well suited to linear mode applications.



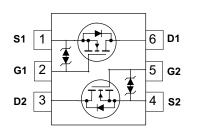
### Features

■ 3.7 A, 20V.  $R_{DS(ON)} = 68 \text{ m}\Omega @ V_{GS} = 4.5V$  $R_{DS(ON)} = 86 \text{ m}\Omega @ V_{GS} = 2.5V$ 

Low profile – 0.8 mm maximum – in the new package MicroFET 2x2 mm

July 2014

- HBM ESD protection level > 2kV (Note 3)
- RoHS Compliant
- Free from halogenated compounds and antimony oxides



### Absolute Maximum Ratings T<sub>A</sub>=25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V <sub>DS</sub>	Drain-Source Voltage		20	V
V <sub>GS</sub>	Gate-Source Voltage		±12	V
I <sub>D</sub>	Drain Current – Continuous	(Note 1a)	3.7	A
	– Pulsed		6	
PD	Power Dissipation for Single Operation	(Note 1a)	1.4	W
		(Note 1b)	0.7	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperat	ture Range	-55 to +150	°C
Therma	I Characteristics	·		•
<b>D</b>	Thermal Desistance, Junction to Ambient		96 (Single Operation)	

D Thermal Desistance Junction to Ambient (11, 11) (Single Operation)	
R <sub>0JA</sub> Thermal Resistance, Junction-to-Ambient(Note 1b)173 (Single Operation)	
R <sub>0JA</sub> Thermal Resistance, Junction-to-Ambient (Note 1c) 69 (Dual Operation)	
R <sub>0JA</sub> Thermal Resistance, Junction-to-Ambient (Note 1d) 151 (Dual Operation)	

### Package Marking and Ordering Information

028 FDMA1028NZ 7" 8mm 3000 unit	Device Marking	Device Marking Device Reel Size		Tape width	Quantity	
	028	FDMA1028NZ	7"	8mm	3000 units	

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Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Char	acteristics		•			
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 V$ , $I_D = 250 \mu A$	20			V
<u>ΔBV<sub>DSS</sub></u> ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	$I_D$ = 250 µA, Referenced to 25°C		15		mV/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	$V_{DS} = 16 V$ , $V_{GS} = 0 V$			1	μA
I <sub>GSS</sub>	Gate–Body Leakage	$V_{GS} = \pm 12 V$ , $V_{DS} = 0 V$			±10	μA
	acteristics (Note 2) Gate Threshold Voltage		0.6	1.0	1.5	V
V <sub>GS(th)</sub>	ů	$V_{DS} = V_{GS}$ , $I_D = 250 \ \mu A$	0.6	1.0	1.5	
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D$ = 250 µA, Referenced to 25°C		-4		mV/°C
R <sub>DS(on)</sub>	Static Drain–Source	$V_{GS} = 4.5 V$ , $I_D = 3.7 A$		37	68	mΩ
	On–Resistance	$V_{GS} = 2.5 V$ , $I_D = 3.3 A$		50	86	
		V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 3.7 A, T <sub>J</sub> =125°C		53	90	
<b>g</b> fs	Forward Transconductance	$V_{DS} = 10 V$ , $I_{D} = 3.7 A$		16		S
Dynamic	Characteristics					
Ciss	Input Capacitance	$V_{DS} = 10 V$ , $V_{GS} = 0 V$ ,		340		pF
Coss	Output Capacitance	f = 1.0 MHz		80		pF
C <sub>rss</sub>	Reverse Transfer Capacitance	1		60		pF
Rg	Gate Resistance				25	Ω

### Switching Characteristics (Note 2)

t <sub>d(on)</sub>	Turn–On Delay Time	V <sub>DD</sub> = 10 V,		8	16	ns
t <sub>r</sub>	Turn–On Rise Time	V <sub>GS</sub> = 4.5 V,	$R_{GEN}$ = 6 $\Omega$	8	16	ns
t <sub>d(off)</sub>	Turn–Off Delay Time	-		14	26	ns
t <sub>f</sub>	Turn–Off Fall Time	-		3	6	ns
Qg	Total Gate Charge	V <sub>DS</sub> = 10 V,	I <sub>D</sub> = 3.7 A,	4	6	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>GS</sub> = 4.5 V		0.7		nC
$Q_{gd}$	Gate-Drain Charge			1.1		nC

FDMA1028NZ Dual N-Channel PowerTrench<sup>®</sup> MOSFET

FDMA1028NZ Rev B7

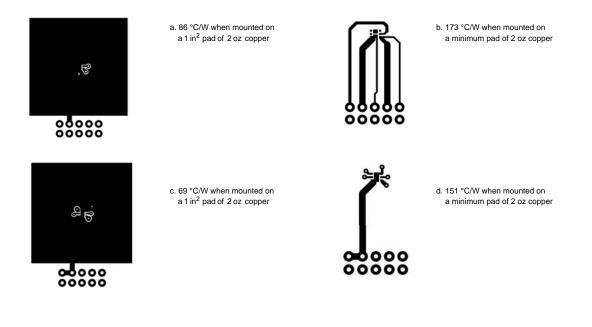
# FDMA1028NZ Dual N-Channel PowerTrench<sup>®</sup> MOSFET

### **Electrical Characteristics** $T_J = 25 \degree C$ unless otherwise noted

### Notes:

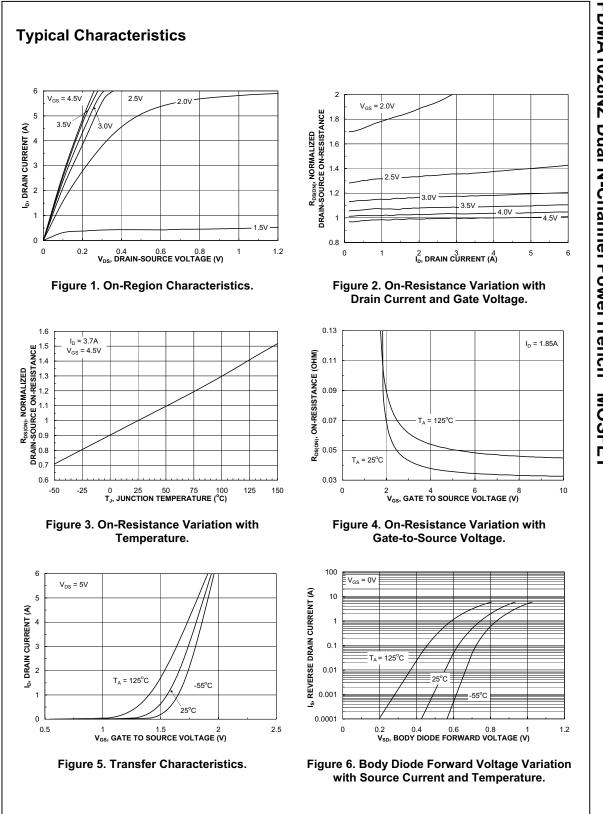
1. R<sub>8JA</sub> is determined with the device mounted on a 1 in<sup>2</sup> oz. copper pad on a 1.5 x 1.5 in. board of FR-4 material. R<sub>8JA</sub> is guaranteed by design while R<sub>8JA</sub> is determined by the user's board design. (a)  $R_{0JA} = 86 \text{ °C/W}$  when mounted on a 1 in<sup>2</sup> pad of 2 oz copper, 1.5 " x 1.5 " x 0.062 " thick PCB. For single operation.

- (b) R<sub>BJA</sub> = 173 °C/W when mounted on a minimum pad of 2 oz copper. For single operation.
- (c)  $R_{0JA} = 69 \text{ °C/W}$  when mounted on a 1 in<sup>2</sup> pad of 2 oz copper, 1.5 " x 1.5 " x 0.062 " thick PCB. For dual operation.
- (d)  $R_{\theta JA}$  = 151  $^{o}\text{C/W}$  when mounted on a minimum pad of 2 oz copper. For dual operation.



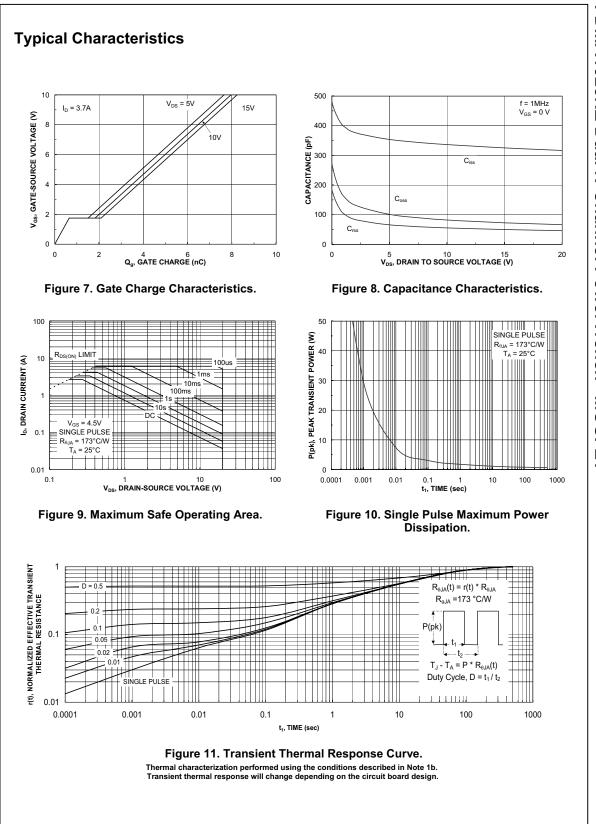
2. Pulse Test : Pulse Width < 300 us, Duty Cycle < 2.0%

3. The diode connected between the gate and source serves only as protection against ESD. No gate overvoltage rating is implied.



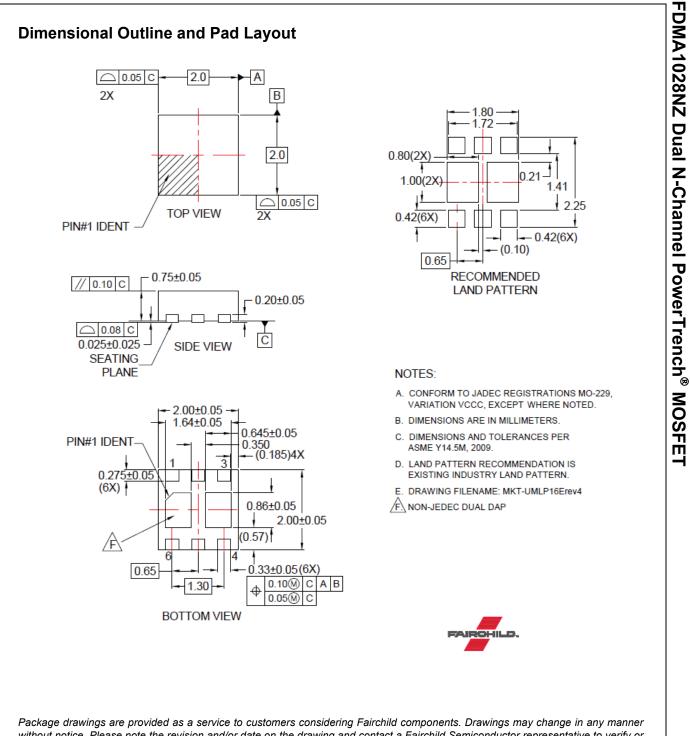
FDMA1028NZ Dual N-Channel PowerTrench<sup>®</sup> MOSFET

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http://www.fairchildsemi.com/package/packageDetails.html?id=PN\_MLDEB-X06



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